George Cirlin

List of Publications by Year
in descending order

333 papers	4,901 citations	101384 36 h-index	118652 62 g-index
333 all docs	333 docs citations	333 times ranked	3210 citing authors

#	Article	IF	Citations
1	Diffusion-induced growth of GaAs nanowhiskers during molecular beam epitaxy: Theory and experiment. Physical Review B, 2005, 71, .	1.1	272
2	Self-catalyzed, pure zincblende GaAs nanowires grown on Si(111) by molecular beam epitaxy. Physical Review B, 2010, 82, .	1.1	194
3	Theoretical analysis of the vapor-liquid-solid mechanism of nanowire growth during molecular beam epitaxy. Physical Review E, 2006, 73, 021603.	0.8	163
4	Gibbs-Thomson and diffusion-induced contributions to the growth rate of Si, InP, and GaAs nanowires. Physical Review B, 2009, 79, .	1.1	163
5	Semiconductor nanowhiskers: Synthesis, properties, and applications. Semiconductors, 2009, 43, 1539-1584.	0.2	158
6	Au-assisted molecular beam epitaxy of InAs nanowires: Growth and theoretical analysis. Journal of Applied Physics, 2007, 102, 094313.	1.1	136
7	New Mode of Vaporâˆ'Liquidâˆ'Solid Nanowire Growth. Nano Letters, 2011, 11, 1247-1253.	4.5	132
8	Critical diameters and temperature domains for MBE growth of IIIâ€"V nanowires on lattice mismatched substrates. Physica Status Solidi - Rapid Research Letters, 2009, 3, 112-114.	1.2	116
9	Kinetics of the initial stage of coherent island formation in heteroepitaxial systems. Physical Review B, 2003, 68, .	1.1	112
10	Growth and Characterization of InP Nanowires with InAsP Insertions. Nano Letters, 2007, 7, 1500-1504.	4.5	110
11	Growth of GaN free-standing nanowires by plasma-assisted molecular beam epitaxy: structural and optical characterization. Nanotechnology, 2007, 18, 385306.	1.3	109
12	Temperature conditions for GaAs nanowire formation by Au-assisted molecular beam epitaxy. Nanotechnology, 2006, 17, 4025-4030.	1.3	107
13	Anapoles in Free-Standing IIIâ€"V Nanodisks Enhancing Second-Harmonic Generation. Nano Letters, 2018, 18, 3695-3702.	4.5	106
14	Role of nonlinear effects in nanowire growth and crystal phase. Physical Review B, 2009, 80, .	1.1	90
15	Facet and in-plane crystallographic orientations of GaN nanowires grown on Si(111). Nanotechnology, 2008, 19, 155704.	1.3	82
16	GaAs nanowires formed by Au-assisted molecular beam epitaxy: Effect of growth temperature. Journal of Crystal Growth, 2007, 301-302, 853-856.	0.7	73
17	Ordering phenomena in InAs strained layer morphological transformation on GaAs (100) surface. Applied Physics Letters, 1995, 67, 97-99.	1.5	67
18	Optical properties of InAs quantum dots in a Si matrix. Applied Physics Letters, 1999, 74, 1701-1703.	1.5	64

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19	Wurtzite to Zinc Blende Phase Transition in GaAs Nanowires Induced by Epitaxial Burying. Nano Letters, 2008, 8, 1638-1643.	4.5	63
20	Atomic Structure of MBE-Grown GaAs Nanowhiskers. Physics of the Solid State, 2005, 47, 2213.	0.2	61
21	Shape modification of III-V nanowires: The role of nucleation on sidewalls. Physical Review E, 2008, 77, 031606.	0.8	59
22	Diffusion-controlled growth of semiconductor nanowires: Vapor pressure versus high vacuum deposition. Surface Science, 2007, 601, 4395-4401.	0.8	57
23	Photovoltaic Properties of p-Doped GaAs Nanowire Arrays Grown on n-Type GaAs(111)B Substrate. Nanoscale Research Letters, 2010, 5, 360-363.	3.1	55
24	Reversibility of the island shape, volume and density in Stranski-Krastanow growth. Semiconductor Science and Technology, 2001, 16, 502-506.	1.0	51
25	Room-temperature light emission from a highly strained Si/Ge superlattice. Applied Physics Letters, 2003, 83, 3084-3086.	1.5	51
26	Formation of InAs quantum dots on a silicon (100) surface. Semiconductor Science and Technology, 1998, 13, 1262-1265.	1.0	50
27	Inorganic photovoltaics â€" Planar and nanostructured devices. Progress in Materials Science, 2016, 82, 294-404.	16.0	50
28	Influence of shadow effect on the growth and shape of InAs nanowires. Journal of Applied Physics, 2012, 111, .	1.1	49
29	The role of surface diffusion of adatoms in the formation of nanowire crystals. Semiconductors, 2006, 40, 1075-1082.	0.2	48
30	On the non-monotonic lateral size dependence of the height of GaAs nanowhiskers grown by molecular beam epitaxy at high temperature. Physica Status Solidi (B): Basic Research, 2004, 241, R30-R33.	0.7	45
31	Photovoltaic properties of GaAsP coreâ€"shell nanowires on Si(001) substrate. Nanotechnology, 2012, 23, 265402.	1.3	45
32	Polar Second-Harmonic Imaging to Resolve Pure and Mixed Crystal Phases along GaAs Nanowires. Nano Letters, 2016, 16, 6290-6297.	4.5	45
33	The diffusion mechanism in the formation of GaAs and AlGaAs nanowhiskers during the process of molecular-beam epitaxy. Semiconductors, 2005, 39, 557-564.	0.2	43
34	Origin of Spontaneous Coreâ€"Shell AlGaAs Nanowires Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 7251-7255.	1.4	42
35	Photoluminescence properties of InAs nanowires grown on GaAs and Si substrates. Nanotechnology, 2010, 21, 335705.	1.3	38
36	Nanowire Quantum Dots Tuned to Atomic Resonances. Nano Letters, 2018, 18, 7217-7221.	4.5	37

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37	Miniband-related 1.4â€“1.8ÂÎ¼m luminescence of Ge/Si quantum dot superlattices. Nanoscale Research Letters, 2006, 1, 137-153.	3.1	36
38	Structure and optical properties of Si/InAs/Si layers grown by molecular beam epitaxy on Si substrate. Applied Physics Letters, 2000, 76, 2677-2679.	1.5	34
39	Effects of the surface preparation and buffer layer on the morphology, electronic and optical properties of the GaN nanowires on Si. Nanotechnology, 2019, 30, 395602.	1.3	31
40	Dopant-stimulated growth of GaN nanotube-like nanostructures on Si(111) by molecular beam epitaxy. Beilstein Journal of Nanotechnology, 2018, 9, 146-154.	1.5	30
41	Room temperature electroluminescence from Ge/Si quantum dots superlattice close to 1.6Î¼m. Physica Status Solidi A, 2003, 198, R4-R6.	1.7	29
42	Kinetic model of the growth of nanodimensional whiskers by the vapor-liquid-crystal mechanism. Technical Physics Letters, 2004, 30, 682-686.	0.2	29
43	Terahertz generation by GaAs nanowires. Applied Physics Letters, 2013, 103, .	1.5	29
44	Droplet epitaxy mediated growth of GaN nanostructures on Si (111) <i>via</i> plasma-assisted molecular beam epitaxy. CrystEngComm, 2018, 20, 3370-3380.	1.3	29
45	Optical study of GaAs quantum dots embedded into AlGaAs nanowires. Semiconductor Science and Technology, 2012, 27, 015009.	1.0	28
46	Growth and Characterization of GaP/GaPAs Nanowire Heterostructures with Controllable Composition. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900350.	1.2	28
47	Photoluminescence properties of GaAs nanowire ensembles with zincblende and wurtzite crystal structure. Physica Status Solidi - Rapid Research Letters, 2010, 4, 175-177.	1.2	27
48	Modified silicone rubber for fabrication and contacting of flexible suspended membranes of n-/p-GaP nanowires with a single-walled carbon nanotube transparent contact. Journal of Materials Chemistry C, 2020, 8, 3764-3772.	2.7	27
49	Numerical modeling of photovoltaic efficiency of n-type GaN nanowires on p-type Si heterojunction. Physica Status Solidi - Rapid Research Letters, 2015, 9, 507-510.	1.2	26
50	Unified mechanism of the surface Fermi level pinning in III-As nanowires. Nanotechnology, 2018, 29, 314003.	1.3	26
51	Transient carrier transfer in tunnel injection structures. Applied Physics Letters, 2008, 93, 031105.	1.5	24
52	Terahertz radiation generation in multilayer quantum-cascade heterostructures. Technical Physics Letters, 2017, 43, 362-365.	0.2	24
53	Growth of Inclined GaAs Nanowires by Molecular Beam Epitaxy: Theory and Experiment. Nanoscale Research Letters, 2010, 5, 1692-1697.	3.1	23
54	InP/Si Heterostructure for High-Current Hybrid Triboelectric/Photovoltaic Generation. ACS Applied Energy Materials, 2019, 2, 4395-4401.	2.5	22

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55	Generation of terahertz radiation in ordered arrays of GaAs nanowires. Applied Physics Letters, 2015, 106, .	1.5	21
56	Control over the parameters of InAs-GaAs quantum dot arrays in the Stranski-Krastanow growth mode. Semiconductors, 2003, 37, 861-865.	0.2	20
57	Fabrication of a terahertz quantum-cascade laser with a double metal waveguide based on multilayer GaAs/AlGaAs heterostructures. Semiconductors, 2016, 50, 1377-1382.	0.2	20
58	Microlens-Enhanced Substrate Patterning and MBE Growth of GaP Nanowires. Semiconductors, 2018, 52, 2088-2091.	0.2	20
59	Structural and Optical Properties of Self-Catalyzed Axially Heterostructured GaPN/GaP Nanowires Embedded into a Flexible Silicone Membrane. Nanomaterials, 2020, 10, 2110.	1.9	20
60	Study of processes of self-catalyzed growth of gaas crystal nanowires by molecular-beam epitaxy on modified Si (111) surfaces. Semiconductors, 2011, 45, 431-435.	0.2	19
61	AlGaAs and AlGaAs/GaAs/AlGaAs nanowires grown by molecular beam epitaxy on silicon substrates. Journal Physics D: Applied Physics, 2017, 50, 484003.	1.3	19
62	Piezoelectric Current Generation in Wurtzite GaAs Nanowires. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1700358.	1.2	19
63	Nanospectroscopic Imaging of Twinning Superlattices in an Individual GaAs-AlGaAs Coreâ€“Shell Nanowire. ACS Photonics, 2014, 1, 1099-1106.	3.2	17
64	Self-Catalyzed MBE-Grown GaP Nanowires on Si(111): V/III Ratio Effects on the Morphology and Crystal Phase Switching. Semiconductors, 2018, 52, 2092-2095.	0.2	17
65	Growth Kinetics of Thin Films Formed by Nucleation during Layer Formation. Semiconductors, 2005, 39, 1267.	0.2	16
66	GaN/AlN freeâ€standing nanowires grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1556-1558.	0.8	16
67	Model of a GaAs Quantum Dot Embedded in a Polymorph AlGaAs Nanowire. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-9.	1.9	16
68	Photoluminescence of isolated quantum dots in metastable InAs arrays. Nanotechnology, 2002, 13, 143-148.	1.3	15
69	Ordering of nanostructures in a Si/Ge0.3Si0.7/Ge system during molecular beam epitaxy. Semiconductors, 2002, 36, 1294-1298.	0.2	15
70	Temperature dependence of the quantum dot lateral size in the Ge/Si(100) system. Physica Status Solidi (B): Basic Research, 2003, 236, R1-R3.	0.7	15
71	Hybrid AlGaAs/GaAs/AlGaAs nanowires with a quantum dot grown by molecular beam epitaxy on silicon. Semiconductors, 2016, 50, 1421-1424.	0.2	15
72	Energy spectrum and thermal properties of a terahertz quantum-cascade laser based on the resonant-phonon depopulation scheme. Semiconductors, 2017, 51, 514-519.	0.2	15

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73	Engineering of the Secondâ€Harmonic Emission Directionality with IIIâ€“V Semiconductor Rod Nanoantennas. Laser and Photonics Reviews, 2020, 14, 2000028.	4.4	15
74	Thermally assisted tunneling processes inInxGa1âˆ’xAsâˆ•GaAsquantum-dot structures. Physical Review B, 2006, 74, .	1.1	14
75	Electron diffraction on GaAs nanowhiskers grown on Si(100) and Si(111) substrates by molecular-beam epitaxy. Physics of the Solid State, 2007, 49, 1440-1445.	0.2	14
76	Control of Conductivity of In_{<i>x</i>}Ga_{1â€“<i>x</i>}As Nanowires by Applied Tension and Surface States. Nano Letters, 2019, 19, 4463-4469.	4.5	14
77	Fabrication of InAs quantum dots on silicon. Technical Physics Letters, 1998, 24, 290-292.	0.2	13
78	Baric properties of InAs quantum dots. Semiconductors, 2008, 42, 1076-1083.	0.2	13
79	Ferromagnetic (Ga,Mn)As nanowires grown by Mn-assisted molecular beam epitaxy. Journal of Applied Physics, 2013, 113, .	1.1	13
80	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. Journal of Physics: Conference Series, 2015, 643, 012115.	0.3	13
81	InAs/InP core/shell nanowire gas sensor: Effects of InP shell on sensitivity and long-term stability. Applied Surface Science, 2019, 498, 143756.	3.1	12
82	Resonant excitation of nanowire quantum dots. Npj Quantum Information, 2020, 6, .	2.8	12
83	Si Incorporation in InP Nanowires Grown by Au-Assisted Molecular Beam Epitaxy. Journal of Nanomaterials, 2009, 2009, 1-7.	1.5	11
84	The initial stage of growth of crystalline nanowhiskers. Semiconductors, 2010, 44, 112-115.	0.2	11
85	Influence of substrate temperature on the shape of GaAs nanowires grown by Au-assisted MOVPE. Journal of Crystal Growth, 2010, 312, 1676-1682.	0.7	11
86	Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. Semiconductors, 2012, 46, 838-841.	0.2	11
87	Formation of (Ga,Mn)As nanowires and study of their magnetic properties. Semiconductors, 2012, 46, 179-183.	0.2	11
88	Effect of postgrowth heat treatment on the structural and optical properties of InP/InAsP/InP nanowires. Semiconductors, 2012, 46, 175-178.	0.2	11
89	Deep-Subwavelength Raman Imaging of the Strained GaP Nanowires. Journal of Physical Chemistry C, 2020, 124, 14054-14060.	1.5	11
90	A3B5 nanowhiskers: MBE growth and properties. European Physical Journal D, 2006, 56, 13-20.	0.4	10

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91	Hexagonal structures in GaAs nanowhiskers. Technical Physics Letters, 2008, 34, 538-541.	0.2	10
92	Sharp emission from single InAs quantum dots grown on vicinal GaAs surfaces. Applied Physics Letters, 2009, 94, 163114.	1.5	10
93	Piezoelectric effect in GaAs nanowires. Semiconductors, 2011, 45, 1082-1084.	0.2	10
94	Composite system based on CdSe/ZnS quantum dots and GaAs nanowires. Semiconductors, 2013, 47, 1346-1350.	0.2	10
95	Piezoelectric effect in wurtzite GaAs nanowires: Growth, characterization, and electromechanical 3D modeling. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 3014-3019.	0.8	10
96	Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. Physics of the Solid State, 2016, 58, 1952-1955.	0.2	10
97	Hybrid GaAs/AlGaAs Nanowireâ€"Quantum dot System for Single Photon Sources. Semiconductors, 2018, 52, 462-464.	0.2	10
98	Nonradiative Energy Transfer in Hybrid Nanostructures with Varied Dimensionality. Semiconductors, 2019, 53, 1258-1261.	0.2	10
99	Hydrogen passivation of the n-GaN nanowire/p-Si heterointerface. Nanotechnology, 2020, 31, 244003.	1.3	10
100	Fabrication and electrical study of large area free-standing membrane with embedded GaP NWs for flexible devices. Nanotechnology, 2020, 31, 46LT01.	1.3	10
101	Thermal Penetration of Gold Nanoparticles into Silicon Dioxide. Acta Physica Polonica A, 2017, 132, 366-369.	0.2	10
102	Light-Emitting Diodes Based on InGaN/GaN Nanowires on Microsphere-Lithography-Patterned Si Substrates. Nanomaterials, 2022, 12, 1993.	1.9	10
103	Si/Ge nanostructures for optoelectronics applications. Physics of the Solid State, 2004, 46, 49-55.	0.2	9
104	Threshold behavior of the formation of nanometer islands in a Ge/Si(100) system in the presence of Sb. Semiconductors, 2005, 39, 547-551.	0.2	9
105	Light-emitting tunneling nanostructures based on quantum dots in a Si and GaAs matrix. Semiconductors, 2012, 46, 1460-1470.	0.2	9
106	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. Materials Science in Semiconductor Processing, 2016, 55, 72-78.	1.9	9
107	Coherent Growth of InP/InAsP/InP Nanowires on a Si (111) Surface by Molecular-Beam Epitaxy. Technical Physics Letters, 2018, 44, 112-114.	0.2	9
108	A new insight into the mechanism of low-temperature Au-assisted growth of InAs nanowires. CrystEngComm, 2019, 21, 4707-4717.	1.3	9

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109	Effect of the Uniaxial Compression on the GaAs Nanowire Solar Cell. Micromachines, 2020, 11, 581.	1.4	9
110	Suppression of dome-shaped clusters during molecular beam epitaxy of Ge on Si(100). Semiconductors, 2004, 38, 1202-1206.	0.2	8
111	GaSb/GaAs quantum dot systems: in situ synchrotron radiation x-ray photoelectron spectroscopy study. Nanotechnology, 2005, 16, 1326-1334.	1.3	8
112	Formation of GaAs nanowhisker arrays by magnetron sputtering deposition. Physics of the Solid State, 2006, 48, 786-791.	0.2	8
113	On diffusion lengths of Ga adatoms on AlAs(111) and GaAs(111) surfaces. Technical Physics, 2009, 54, 586-589.	0.2	8
114	Current-voltage characteristics of silicon-doped GaAs nanowhiskers with a protecting AlGaAs coating overgrown with an undoped GaAs layer. Semiconductors, 2010, 44, 610-615.	0.2	8
115	Temperature dependent luminescence from quantum dot arrays: phonon-assisted line broadening versus carrier escape-induced narrowing. Physica Status Solidi (B): Basic Research, 2010, 247, 347-352.	0.7	8
116	Piezoelectric effect in GaAs nanowires: experiment and theory. Physica Status Solidi - Rapid Research Letters, 2016, 10, 172-175.	1.2	8
117	Multilayer heterostructures for quantum-cascade lasers operating in the terahertz frequency range. Semiconductors, 2016, 50, 662-666.	0.2	8
118	Numerical simulation of the properties of solar cells based on GaPNAs/Si heterostructures and GaN nanowires. Semiconductors, 2016, 50, 1521-1525.	0.2	8
119	The Role of Physical Models in the Description of Luminescence Kinetics of Hybrid Nanowires. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2020, 128, 119-124.	0.2	8
120	Tailoring Morphology and Vertical Yield of Self-Catalyzed GaP Nanowires on Template-Free Si Substrates. Nanomaterials, 2021, 11, 1949.	1.9	8
121	Red GaPAs/GaP Nanowire-Based Flexible Light-Emitting Diodes. Nanomaterials, 2021, 11, 2549.	1.9	8
122	Stoichiometry and absolute atomic concentration profiles obtained by combined Rutherford backscattering spectroscopy and secondary-ion mass spectroscopy: InAs nanocrystals in Si. Nanotechnology, 2002, 13, 631-634.	1.3	7
123	Optical properties of structures with ultradense arrays of Ge QDs in an Si matrix. Semiconductors, 2003, 37, 210-214.	0.2	7
124	Dependence of structural and optical properties of QD arrays in an InAs/GaAs system on surface temperature and growth rate. Semiconductors, 2004, 38, 329-334.	0.2	7
125	Properties of GaAs nanowhiskers grown on a GaAs(111)B surface using a combined technique. Semiconductors, 2004, 38, 1217-1220.	0.2	7
126	The effective thickness, temperature and growth rate behavior of quantum dot ensembles. Physica Status Solidi (B): Basic Research, 2004, 241, R42-R45.	0.7	7

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127	MBE-Grown Si : Er Light-Emitting Structures: Effect of Epitaxial Growth Conditions on Impurity Concentration and Photoluminescence. Physics of the Solid State, 2005, 47, 113.	0.2	7
128	Growth of GaAs nanowhisker arrays by magnetron sputtering on Si(111) substrates. Technical Physics Letters, 2006, 32, 520-522.	0.2	7
129	Tuning of the interdot resonance in stacked InAs quantum dot arrays by an external electric field. Journal of Applied Physics, 2006, 100, 083704.	1.1	7
130	Selective-Area Growth of GaN Nanowires on Patterned SiOx/Si Substrates by Molecular Beam Epitaxy. Technical Physics Letters, 2020, 46, 1080-1083.	0.2	7
131	Selective Area Epitaxy of GaN Nanowires on Si Substrates Using Microsphere Lithography: Experiment and Theory. Nanomaterials, 2022, 12, 2341.	1.9	7
132	Optical properties of submonolayer germanium clusters formed by molecular-beam epitaxy in a silicon matrix. Technical Physics Letters, 2001, 27, 14-16.	0.2	6
133	Localization of Holes in an InAsâˆ•GaAs Quantum-Dot Molecule. Semiconductors, 2005, 39, 119.	0.2	6
134	Influence of Antimony on the Morphology and Properties of an Array of Geâˆ•Si(100) Quantum Dots. Physics of the Solid State, 2005, 47, 58.	0.2	6
135	The transition from thermodynamically to kinetically controlled formation of quantum dots in an InAs/GaAs(100) system. Semiconductors, 2005, 39, 820-825.	0.2	6
136	Intraband light absorption in InAs/GaAs quantum dots covered with InGaAs quantum wells. Semiconductor Science and Technology, 2006, 21, 1341-1347.	1.0	6
137	Coupling of electron states in the InAs/GaAs quantum dot molecule. Semiconductors, 2006, 40, 331-337.	0.2	6
138	(In,Mn)As quantum dots: Molecular-beam epitaxy and optical properties. Semiconductors, 2013, 47, 1037-1040.	0.2	6
139	Photoelectric properties of an array of axial GaAs/AlGaAs nanowires. Technical Physics Letters, 2015, 41, 443-447.	0.2	6
140	Electronic structure of (In,Mn)As quantum dots buried in GaAs investigated by soft-x-ray ARPES. Nanotechnology, 2016, 27, 425706.	1.3	6
141	Terahertz Quantum-Cascade Laser Based on the Resonant-Phonon Depopulation Scheme. International Journal of High Speed Electronics and Systems, 2016, 25, 1640022.	0.3	6
142	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate. AIP Conference Proceedings, 2016, , .	0.3	6
143	GaAs Wurtzite Nanowires for Hybrid Piezoelectric Solar Cells. Semiconductors, 2018, 52, 609-611.	0.2	6
144	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. Nanotechnology, 2018, 29, 045602.	1.3	6

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145	Luminescence Photodynamics of Hybrid-Structured InP/InAsP/InP Nanowires Passivated by a Layer of TOPO-CdSe/ZnS Quantum Dots. Semiconductors, 2020, 54, 1141-1146.	0.2	6
146	Anisotropic Radiation in Heterostructured â€œEmitter in a Cavityâ€•Nanowire. Nanomaterials, 2022, 12, 241.	1.9	6
147	Effect of growth conditions on InAs nanoislands formation on Si(100) surface. European Physical Journal D, 1999, 49, 1547-1552.	0.4	5
148	Room temperature electroluminescence from multilayer GeSi heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1390-1394.	0.8	5
149	Influence of MBE growth conditions on the surface morphology of Al(Ga)As nanowhiskers. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1365-1369.	0.8	5
150	The theory of the formation of multilayered thin films on solid surfaces. Semiconductors, 2006, 40, 249-256.	0.2	5
151	DLTS study of the Wannierâ€“Stark effect in Ge/Si QD superlattices. Physica B: Condensed Matter, 2007, 401-402, 576-579.	1.3	5
152	Effect of deposition conditions on nanowhisker morphology. Semiconductors, 2007, 41, 865-874.	0.2	5
153	InGaAs tunnel-injection structures with nanobridges: Excitation transfer and luminescence kinetics. Semiconductors, 2010, 44, 1050-1058.	0.2	5
154	Specific features of Raman spectra of IIIâ€“V nanowhiskers. Physics of the Solid State, 2011, 53, 1431-1439.	0.2	5
155	Tunnel injection emitter structures with barriers comprising nanobridges. Physica Status Solidi - Rapid Research Letters, 2011, 5, 385-387.	1.2	5
156	Resonant features of the terahertz generation in semiconductor nanowires. Semiconductors, 2016, 50, 1561-1565.	0.2	5
157	Work function tailoring in gallium phosphide nanowires. Applied Surface Science, 2021, 563, 150018.	3.1	5
158	Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. Semiconductors, 2020, 54, 1092-1095.	0.2	5
159	1.3-1.4 Âµm photoluminescence emission from InAs/GaAs quantum dot multilayer structures grown on GaAs singular and vicinal substrates. Nanotechnology, 2000, 11, 323-326.	1.3	4
160	Quantum dots in InAs layers of subcritical thickness on GaAs(100). Technical Physics Letters, 2003, 29, 691-693.	0.2	4
161	Diffusion-barrier contacts based on the TiN and Ti(Zr)Bx interstitial phases in the microwave diodes for the range of 75â€“350 GHz. Semiconductors, 2006, 40, 734-738.	0.2	4
162	Charge and spin storage in self-organized quantum dots. Applied Physics Letters, 2006, 88, 182107.	1.5	4

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163	Interband light absorption and Pauli blocking in InAs/GaAs quantum dots covered by InGaAs quantum wells. Semiconductor Science and Technology, 2007, 22, 814-818.	1.0	4
164	Deposition-rate dependence of the height of GaAs-nanowires. Semiconductors, 2008, 42, 1259-1263.	0.2	4
165	Computer simulation of the structure and raman spectra of GaAs polytypes. Physics of the Solid State, 2013, 55, 1220-1230.	0.2	4
166	(In,Mn)As multilayer quantum dot structures. Applied Physics Letters, 2014, 105, .	1.5	4
167	Solar Cell Based on Core/Shell Nanowires. Semiconductors, 2018, 52, 1568-1572.	0.2	4
168	Electromechanical Switch Based on InxGa1 â€"xAs Nanowires. Semiconductors, 2018, 52, 1833-1835.	0.2	4
169	Core-Shell III-Nitride Nanowire Heterostructure: Negative Differential Resistance and Device Application Potential. Semiconductors, 2018, 52, 489-492.	0.2	4
170	Synthesis by Molecular Beam Epitaxy and Properties of InGaN Nanostructures of Branched Morphology on a Silicon Substrate. Technical Physics Letters, 2019, 45, 1111-1113.	0.2	4
171	Influence of TOPO and TOPO-CdSe/ZnS Quantum Dots on Luminescence Photodynamics of InP/InAsP/InPHeterostructure Nanowires. Nanomaterials, 2021, 11, 640.	1.9	4
172	Effect of crystal structure on the Youngâ€™s modulus of GaP nanowires. Nanotechnology, 2021, 32, 385706.	1.3	4
173	The effect of postgrowth annealing on the structure and optical properties of multilayer Ge/Si heterostructures. Technical Physics Letters, 2003, 29, 739-742.	0.2	3
174	Carrier density profile in weakly coupled GaAs/AlGaAs superlattices. Semiconductors, 2004, 38, 451-454.	0.2	3
175	Wannier-stark effect in Ge/Si quantum dot superlattices. Semiconductors, 2008, 42, 305-309.	0.2	3
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